Low-Voltage, Low r_{ON}, Single Analog Switch In miniQFN-6 Package

DESCRIPTION

The DG2511/DG2512/DG2513 are low on-resistance, single-pole/double-throw or single-pole/single-throw monolithic CMOS analog switch. It is designed for low voltage applications. The DG2511/DG2512/DG2513 are ideal for portable and battery powered equipment, requiring high performance and efficient use of board space. In additional to the low on-resistance (1.3 Ω at 2.7 V).

The DG2511 is an SPDT and the DG2512/DG2513 are SPST. The switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

The DG2511/DG2512/DG2513 are built on Vishay Siliconix's low voltage JI5L process. An epitaxial layer prevents latchup.

Break-before-make is guaranteed.

The DG2511/DG2512/DG2513 represents a breakthrough in packaging development for analog switching products. The miniQFN-6 package (1.2 x 1.0 mm).

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For analog switching products manufactured with NiPdAu device terminations, the lead (Pb)-free "-E4" suffix is being used as a designator.

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance - r_{ON}: 1.3 Ω at 2.7 V
- Low Charge Injection
- Low Voltage Logic Compatible
- miniQFN-6 Package (1.2 x 1.0 mm)

Pb-free
RoHS COMPLIANT

BENEFITS

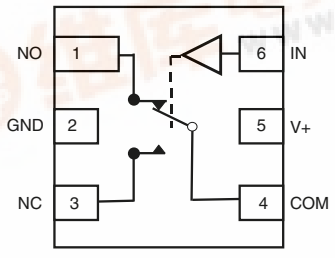
- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space
- Guaranteed 2 V Operation

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits
- ADC and DAC Applications
- Low Voltage Data Acquisition Systems

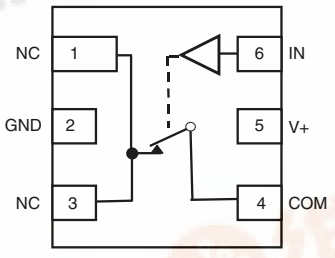
FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

DG2511 miniQFN-6



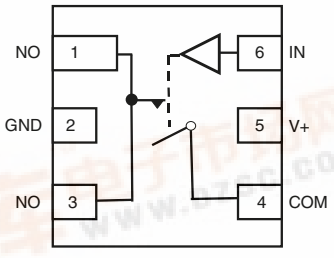
Top View

DG2512 miniQFN-6

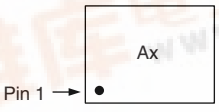


Top View

DG2513 miniQFN-6



Top View



Device Marking: Ax for DG2511
Bx for DG2512
Cx for DG2513
x = Date/Lot Traceability Code
Note: Pin 1 has long lead

TRUTH TABLE

Logic	NC	NO
0	ON	OFF
1	OFF	ON

COMMERCIAL ORDERING INFORMATION

Temp Range	Package	Part Number
- 40 to 85 °C	miniQFN-6 Lead (Pb)-free with Tape and Reel	DG2511DN-T1-E4 DG2512DN-T1-E4 DG2513DN-T1-E4

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Reference V+ to GND			- 0.3 to + 6	V
IN, COM, NC, NO[a]			- 0.3 to (V+ + 0.3 V)	
Continuous Current (NO, NC, COM pins)			± 150	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)			± 300	
Storage Temperature	D Suffix		- 65 to 150	°C
Power Dissipation (Packages)[b]	miniQFN-6[c]		160	mW

Notes:
a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate 2.0 mW/°C above 70 °C.

SPECIFICATIONS (V+ = 3 V)							
Parameter	**Symbol**	**Test Conditions Otherwise Unless Specified** V+ = 3 V, ± 10 %, V_{IN} = 0.4 V or 2.0 V[e]	**Temp[a]**	**Limits - 40 to 85 °C** **Min[b]**	**Typ[c]**	**Max[b]**	**Unit**
Analog Switch							
Analog Signal Range[d]	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V
On-Resistance	r_{ON}	V+ = 2.7 V, V_{COM} = 0.5 V/1.5 V, I_{NO}, I_{NC} = 100 mA	Room Full		1.4	1.7 1.9	Ω
r_{ON} Match	Δr_{ON}		Room			0.15	
r_{ON} Flatness	r_{ON} Flatness		Room		0.3	0.4	
Switch Off Leakage Current[f]	$I_{NO(off)}$ $I_{NC(off)}$	V+ = 3.3 V, V_{NO}, V_{NC}= 1 V/3 V, V_{COM} = 3 V/1 V	Room Full	- 2 - 20		2 20	nA
	$I_{COM(off)}$		Room Full	- 2 - 20		2 20	
Channel-On Leakage Current[f]	$I_{COM(on)}$	V+ = 3.3 V, V_{NO}, V_{NC} = V_{COM} = 1 V/3 V	Room Full	- 2 - 20		2 20	
Digital Control							
Input High Voltage	V_{INH}		Full	1.6			V
Input Low Voltage	V_{INL}		Full			0.4	
Input Capacitance	C_{in}		Full		4		pF
Input Current	I_{INL} or I_{INH}	V_{IN} = 0 or V+	Full	1		1	µA
Dynamic Characteristics							
Turn-On Time	t_{ON}	V+ = 2.7 V, V_{NO} or V_{NC} = 1.5 V, R_L = 50 Ω, C_L = 35 pF	Room Full		18	43 49	ns
Turn-Off Time	t_{OFF}		Room Full		7	32 34	
Break-Before-Make Time	t_{BBM}		Room	1	12		
Charge Injection[d]	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		3		pC
Off-Isolation[d]	OIRR	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz	Room		- 58		dB
Crosstalk[d]	X_{TALK}		Room		- 64		
N_O, N_C Off Capacitance[d]	$C_{NO(off)}$ $C_{NC(off)}$	V_{IN} = 0 or V+, f = 1 MHz	Room		21		pF
Channel-On Capacitance[d]	C_{ON}		Room		61		
Power Supply							
Power Supply Range	V+			1.8		5.5	V
Power Supply Current	I+	V_{IN} = 0 or V+			0.01	1.0	µA

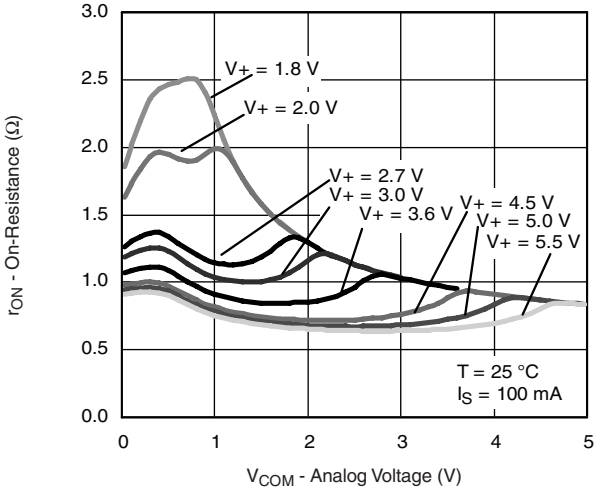
SPECIFICATIONS (V+ = 5.0 V)

Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 5.0 V, ± 10 %, V_{IN} = 0.6 V or 1.8 V[e]	Temp[a]	Limits - 40 to 85 °C Min[b]	Typ[c]	Max[b]	Unit
Analog Switch							
Analog Signal Range[d]	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V
On-Resistance	r_{ON}	V+ = 4.5 V, V_{COM} = 0.5 V/2.5 V, I_{NO}, I_{NC} = 100 mA	Room Full		1	1.3 1.45	Ω
r_{ON} Match	Δr_{ON}		Room			0.15	
r_{ON} Flatness	r_{ON} Flatness		Room		0.3	0.4	
Switch Off Leakage Current	$I_{NO(off)}$ $I_{NC(off)}$	V+ = 5.5 V, V_{NO}, V_{NC}= 1 V/4.5 V, V_{COM} = 4.5 V/1.0 V	Room Full	- 2 - 20		2 20	nA
	$I_{COM(off)}$		Room Full	- 2 - 20		2 20	
Channel-On Leakage Current	$I_{COM(on)}$	V+ = 5.5 V, V_{NO}, V_{NC} = V_{COM} = 1.0 V/4.5 V	Room Full	- 2 - 20		2 20	
Digital Control							
Input High Voltage	V_{INH}		Full	1.8			V
Input Low Voltage	V_{INL}		Full			0.6	
Input Capacitance	C_{in}		Full		4		pF
Input Current	I_{INL} or I_{INH}	V_{IN} = 0 or V+	Full	1		1	µA
Dynamic Characteristics							
Turn-On Time	t_{ON}	V_{NO} or V_{NC} = 2.5 V, R_L = 50 Ω, C_L = 35 pF	Room Full		11	35 39	ns
Turn-Off Time	t_{OFF}		Room Full		6	31 33	
Break-Before-Make Time	t_{BBM}		Room	1	5		
Charge Injection[d]	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		14		pC
Off-Isolation[d]	OIRR	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz	Room		- 58		dB
Crosstalk[d]	X_{TALK}		Room		- 64		
N_O, N_C Off Capacitance[d]	$C_{NO(off)}$ $C_{NC(off)}$	V_{IN} = 0 or V+, f = 1 MHz	Room		19		pF
Channel-On Capacitance[d]	C_{ON}		Room		61		
Power Supply							
Power Supply Range	V+	V_{IN} = 0 or V+		1.8		5.5	V
Power Supply Current	I+				0.01	1.0	µA

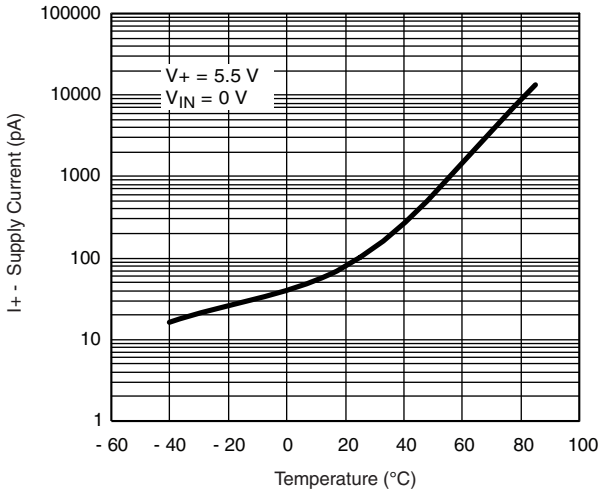
Notes:
a. Room = 25 °C, Full = as determined by the operating suffix.
b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
c. Typical values are for design aid only, not guaranteed nor subject to production testing.
d. Guarantee by design, nor subjected to production test.
e. VIN = input voltage to perform proper function.
f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

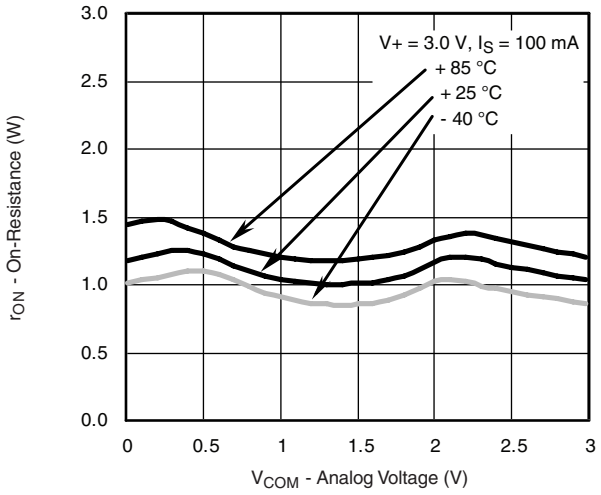
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



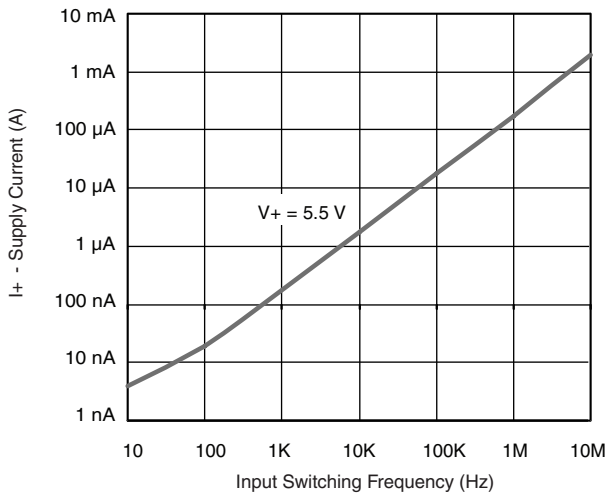
r_{ON} vs. V_{COM} and Supply Voltage



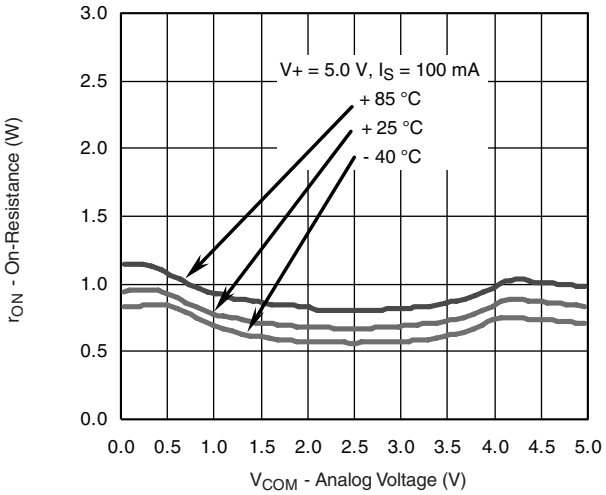
Supply Current vs. Temperature



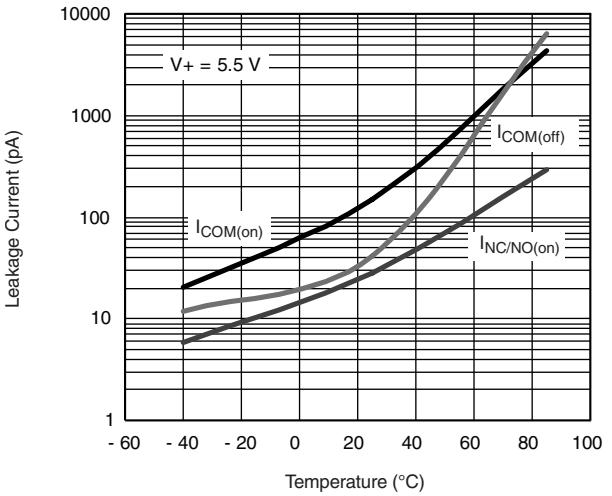
r_{ON} vs. Analog Voltage and Temperature



Supply Current vs. Input Switching Frequency

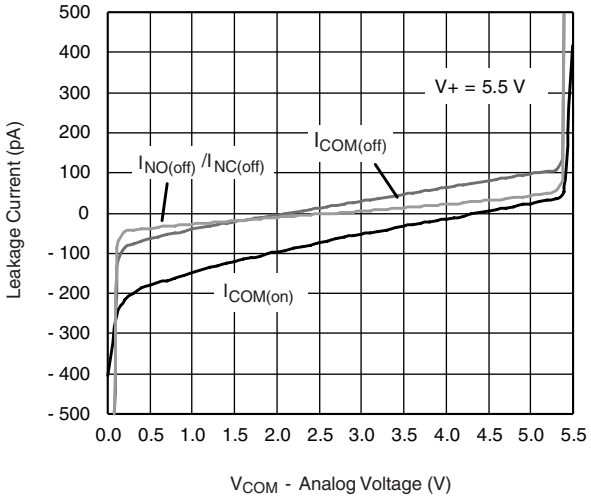


r_{ON} vs. Analog Voltage and Temperature

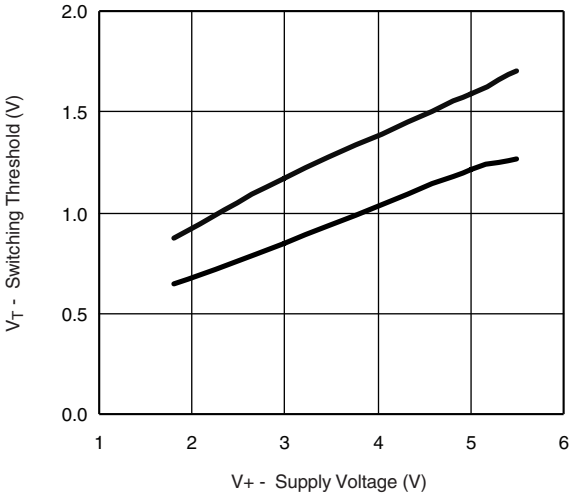


Leakage Current vs. Temperature

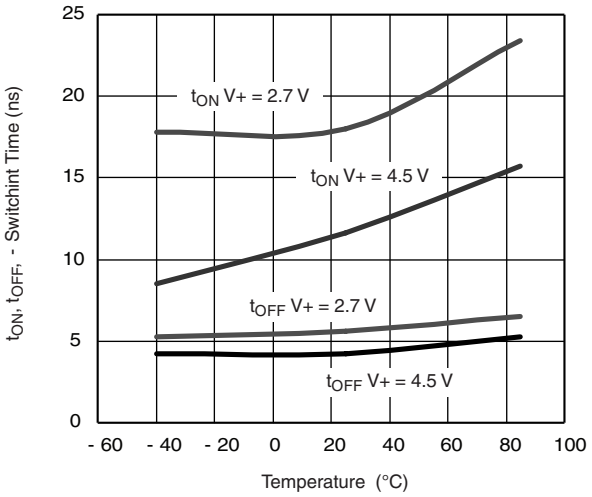
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



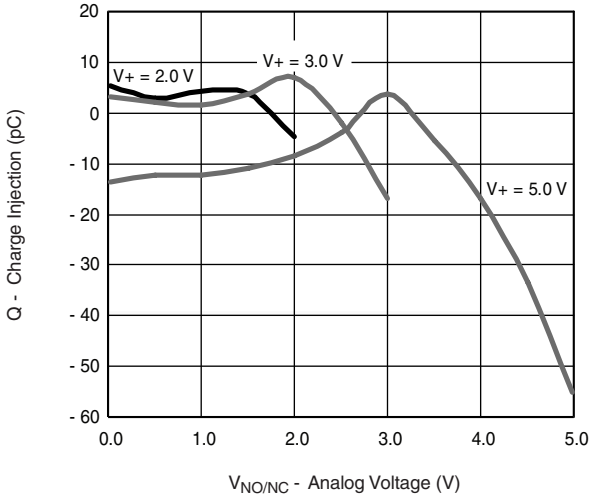
Leakage vs. Analog Voltage



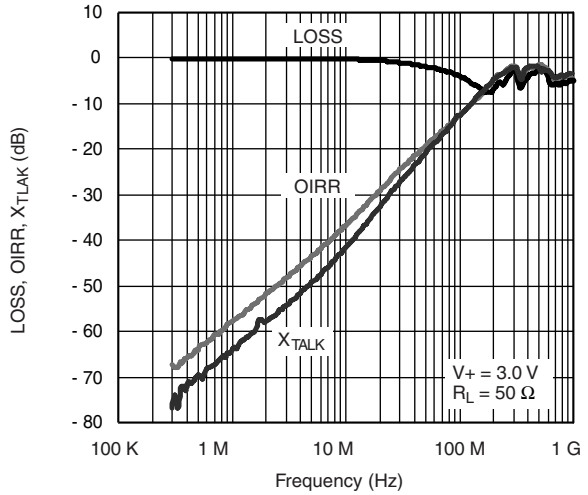
Switching Threshold vs. Supply Voltage



Switching Time vs. Temperature and Supply Voltage

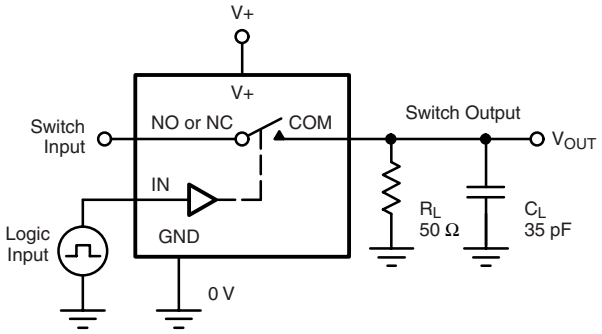


Charge Injection vs. Analog Voltage



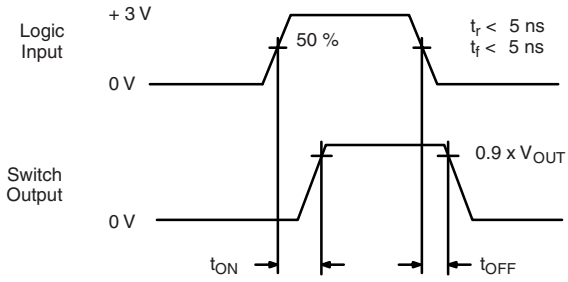
Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

TEST CIRCUITS



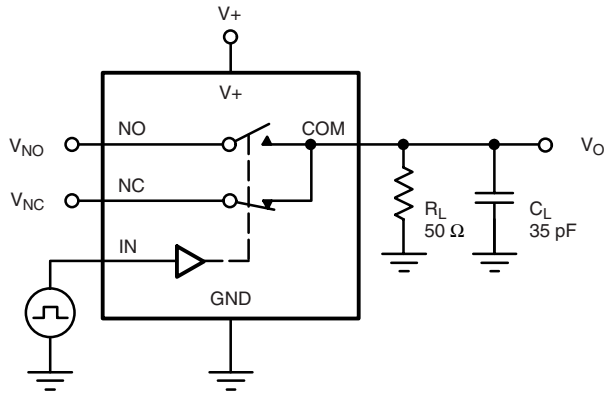
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM}\left(\frac{R_L}{R_L + R_{ON}}\right)$$



Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time



C_L (includes fixture and stray capacitance)

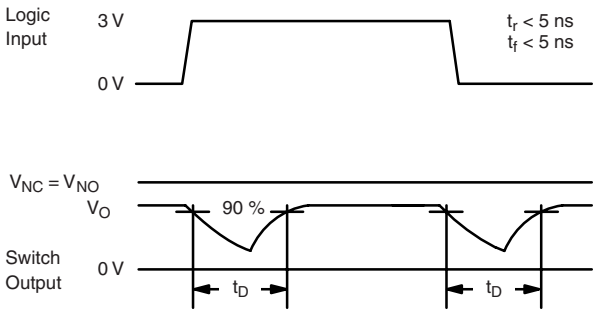
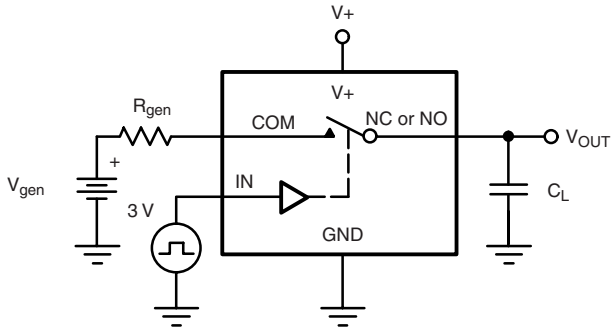
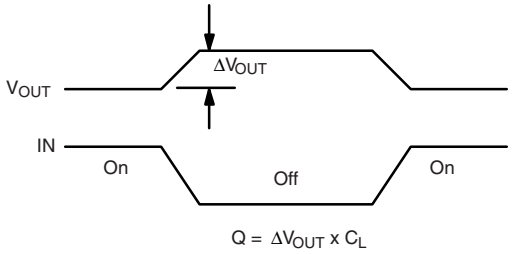


Figure 2. Break-Before-Make Interval





Q = ΔV_{OUT} x C_L

IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

TEST CIRCUITS

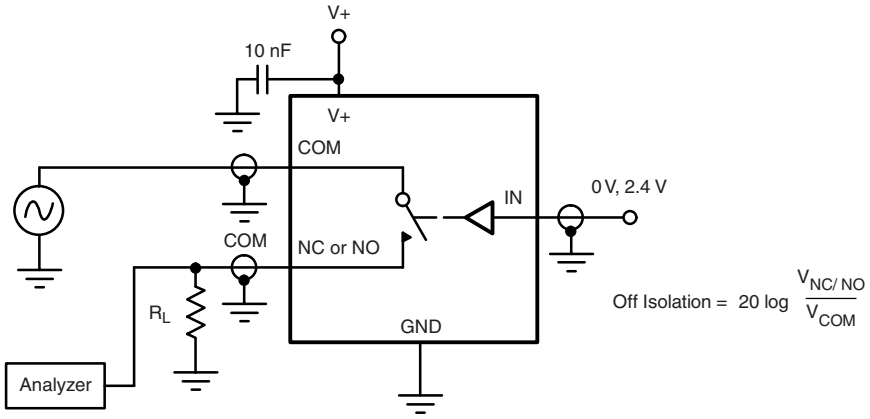


Figure 4. Off-Isolation

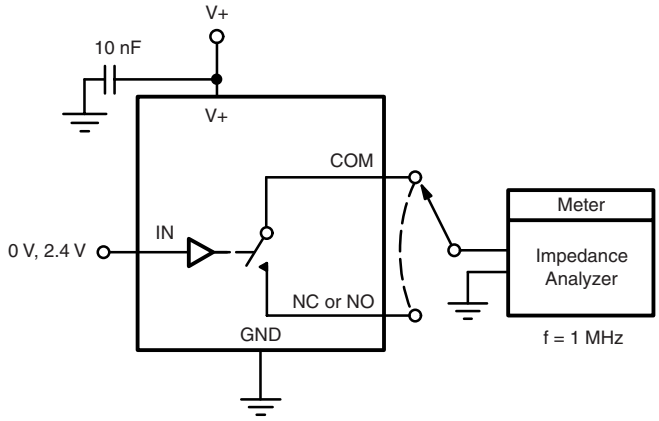


Figure 5. Channel Off/On Capacitance

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